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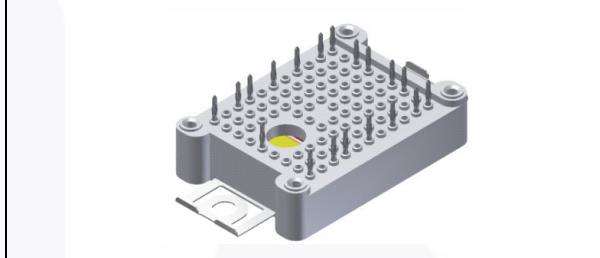
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# FPF1C2P5MF07AM

## F1 Module solution for PV-Application

### General Description

Fairchild's brand-new DC-AC module is designed for a power stage that needs more compact design. And the Press-fit technology provides simple and reliable mounting. This module is optimized for the application such as solar inverter where a high efficiency and robust design are needed.



Package Code: F1

### Electrical Features

- High Efficiency
- Low Conduction and Switching losses
- Low  $V_{CE(sat)}$  : 1.1 V typ. @  $I_c = 30$  A
- Low  $R_{DS(ON)}$  : 90 m $\Omega$  max.
- Fast Recovery Body Diode

### Mechanical Features

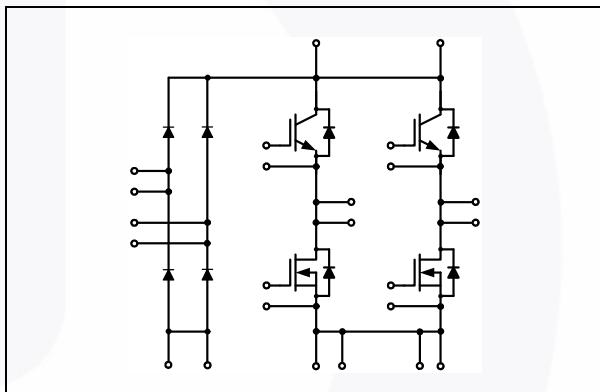
- Compact size : F1 Package
- Press-fit contact technology

### Applications

- Solar Inverter

### Certification

- UL approved (E209204)



Internal Circuit Diagram

### Absolute Maximum Ratings

$T_C = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Description	Rating	Units
<b>Rectifier Diode</b>			
$V_{RRM}$	Peak Repetitive Reverse Voltage	620	V
$I_{Fav}$	Diode Continuous Forward Current @ $T_C = 80^\circ\text{C}$	27	A
$I_{FSM}$	Diode Maximum Forward Surge Current	245	A
$I^2t$	$I^2t$ value	300	$\text{A}^2\text{s}$
$P_D$	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	77	W
$T_J$	Operating Junction Temperature	-40 to +150	$^\circ\text{C}$

**Absolute Maximum Ratings**  $T_C = 25^\circ\text{C}$  unless otherwise noted. (Continued)

Symbol	Description	Rating	Units
<b>High-side IGBT</b>			
$V_{CES}$	Collector-Emitter Voltage	620	V
$V_{GES}$	Gate-Emitter Voltage	$\pm 20$	V
$I_C$	Collector Current $\text{@ } T_C = 80^\circ\text{C}$	39	A
$I_{CM}$	Pulsed Collector Current	90	A
$I_F$	Diode Continuous Forward Current $\text{@ } T_C = 80^\circ\text{C}$	22	A
$I_{FM}$	Diode Maximum Forward Current	90	A
$P_D$	Maximum Power Dissipation $\text{@ } T_C = 25^\circ\text{C}$	231	W
$T_J$	Operating Junction Temperature	-40 to +150	$^\circ\text{C}$
<b>Low-side MOSFET</b>			
$V_{DSS}$	Drain-Source Voltage	620	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Continuous Drain Current $\text{@ } T_C = 25^\circ\text{C}$	36	A
	$\text{@ } T_C = 80^\circ\text{C}$	27	A
$I_{DM}$	Pulsed Drain Current Limited by $T_J$ max.	156	A
$I_S$	Continuous Source-Drain Forward Current	36	A
$I_{SM}$	Maximum Pulsed Source-Drain Forward Current	156	A
$P_D$	Maximum Power Dissipation $\text{@ } T_C = 25^\circ\text{C}$	250	W
$T_J$	Operating Junction Temperature	-40 to +150	$^\circ\text{C}$
<b>Module</b>			
$T_{STG}$	Storage Temperature	-40 to +125	$^\circ\text{C}$
$V_{ISO}$	Isolation Voltage $\text{@ AC } 1_{\text{MIN}}$	2500	V
Iso._Material	Internal Isolation Material	$\text{Al}_2\text{O}_3$	
$F_{MOUNT}$	Mounting Force per Clamp	20 to 50	N
Weight	Typ.	22	g
Creepage	Terminal to Heatsink	11.5	mm
	Terminal to Terminal	6.3	mm
Clearance	Terminal to Heatsink	10.0	mm
	Terminal to Terminal	5.0	mm

**Package Marking and Ordering Information**

Device	Device Marking	Package	Packing Type	Quantity / Tray
FPF1C2P5MF07AM	FPF1C2P5MF07AM	F1	Tray	22

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
<b>Rectifier Diode</b>						
$V_F$	Diode Forward Voltage	$I_F = 30 \text{ A}$	-	-	1.9	V
		$I_F = 30 \text{ A} @ T_C = 125^\circ\text{C}$	-	1.45	-	V
$I_R$	Reverse Leakage Current	$V_R = 620 \text{ V}$	-	-	25	$\mu\text{A}$
$R_{\theta\text{JC}}$	Thermal Resistance of Junction to Case	per Diode	-	-	1.62	$^\circ\text{C/W}$
<b>High-side IGBT</b>						
<b>Off Characteristics</b>						
$BV_{CES}$	Collector-Emitter Breakdown Voltage	$V_{GE} = 0 \text{ V}, I_C = 1 \text{ mA}$	620	-	-	V
$I_{CES}$	Collector Cut-off Current	$V_{CE} = V_{CES}, V_{GE} = 0 \text{ V}$	-	-	25	$\mu\text{A}$
$I_{GES}$	Gate-Emitter Leakage Current	$V_{GE} = V_{GES}, V_{CS} = 0 \text{ V}$	-	-	2.5	$\mu\text{A}$
<b>On Characteristics</b>						
$V_{GE(\text{th})}$	Gate-Emitter Threshold Voltage	$V_{GE} = V_{CE}, I_C = 30 \text{ mA}$	4	5.7	7	V
$V_{CE(\text{sat})}$	Collector-Emitter Saturation Voltage	$I_C = 30 \text{ A}, V_{GE} = 15 \text{ V}$	-	1.1	1.6	V
		$I_C = 30 \text{ A}, V_{GE} = 15 \text{ V} @ T_C = 125^\circ\text{C}$	-	1.0	-	V
		$I_C = 60 \text{ A}, V_{GE} = 15 \text{ V}$	-	1.4	-	V
<b>Switching Characteristics</b>						
$Q_g$	Total Gate Charge	$V_{DS} = 380 \text{ V}, V_{GS} = 0\text{V}...+15 \text{ V}, I_D = 30 \text{ A}$	-	214	-	nC
$R_{\theta\text{JC}}$	Thermal Resistance of Junction to Case	per IGBT	-	-	0.54	$^\circ\text{C/W}$

\* Note : High-side IGBT is optimized for line frequency switching such as 50/60 Hz.

<b>High-Side FWD</b>						
$V_{FM}$	Diode Forward Voltage	$I_F = 15 \text{ A}, V_{GS} = 0 \text{ V}$	-	1.75	2.25	V
$t_{rr}$	Reverse Recovery Time	$I_F = 15 \text{ A}$	-	30	-	ns
$I_{rr}$	Reverse Recovery Current	$dI_F/dt = 1650 \text{ A}/\mu\text{s}$	-	27	-	A
$Q_{rr}$	Reverse Recovery Charge		-	405	-	nC
$t_{rr}$	Reverse Recovery Time		-	43	-	ns
$I_{rr}$	Reverse Recovery Current	$dI_F/dt = 1500 \text{ A}/\mu\text{s} @ T_C = 125^\circ\text{C}$	-	38	-	A
$Q_{rr}$	Reverse Recovery Charge		-	814	-	nC
$R_{\theta\text{JC}}$	Thermal Resistance of Junction to Case	per Diode	-	-	1.61	$^\circ\text{C/W}$

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted. (Continued)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
<b>Low-Side MOSFET</b>						
<b>Off Characteristics</b>						
$\text{BV}_{\text{DSS}}$	Drain-Source Breakdown Voltage	$\text{V}_{\text{GS}} = 0 \text{ V}$ , $\text{I}_D = 1 \text{ mA}$	620	-	-	V
$\text{I}_{\text{DSS}}$	Zero Gate Voltage Drain Current	$\text{V}_{\text{DS}} = 620 \text{ V}$ , $\text{V}_{\text{GS}} = 0 \text{ V}$	-	-	25	$\mu\text{A}$
$\text{I}_{\text{GSS}}$	Gate-Body Leakage Current, Forward	$\text{V}_{\text{GS}} = 20 \text{ V}$ , $\text{V}_{\text{DS}} = 0 \text{ V}$			2.5	$\mu\text{A}$
<b>On Characteristics</b>						
$\text{V}_{\text{GS(th)}}$	Gate-Source Threshold Voltage	$\text{V}_{\text{GS}} = \text{V}_{\text{DS}}$ , $\text{I}_D = 250 \text{ mA}$	2.7	3.8	5.3	V
$\text{R}_{\text{DS(ON)}}$	Static Drain-Source On-Resistance	$\text{I}_D = 27 \text{ A}$ , $\text{V}_{\text{GS}} = 10 \text{ V}$	-	-	90	$\text{m}\Omega$
		$\text{I}_D = 27 \text{ A}$ , $\text{V}_{\text{GS}} = 10 \text{ V}$ @ $T_C = 125^\circ\text{C}$	-	135	-	$\text{m}\Omega$
		$\text{I}_D = 47 \text{ A}$ , $\text{V}_{\text{GS}} = 10 \text{ V}$	-	76	-	$\text{m}\Omega$
$\text{V}_{\text{SD}}$	Source-Drain Diode Forward Voltage	$\text{I}_{\text{SD}} = 27 \text{ A}$ , $\text{V}_{\text{GS}} = 0 \text{ V}$	-	-	1.5	V
		$\text{I}_{\text{SD}} = 47 \text{ A}$ , $\text{V}_{\text{GS}} = 0 \text{ V}$	-	1.3	-	V
<b>Switching Characteristics</b>						
$t_{\text{d(on)}}$	Turn-On Delay Time	$\text{V}_{\text{CC}} = 380 \text{ V}$ $\text{I}_D = 27 \text{ A}$ $\text{V}_{\text{GS}} = 10 \text{ V}$ $\text{R}_G = 10 \Omega$ Inductive Load $T_C = 25^\circ\text{C}$	-	57	-	ns
$t_r$	Rise Time		-	14	-	ns
$t_{\text{d(off)}}$	Turn-Off Delay Time		-	240	-	ns
$t_f$	Fall Time		-	20	-	ns
$E_{\text{ON}}$	Turn-On Switching Loss per Pulse		-	440	-	$\mu\text{J}$
$E_{\text{OFF}}$	Turn-Off Switching Loss per Pulse		-	113	-	$\mu\text{J}$
$t_{\text{d(on)}}$	Turn-On Delay Time	$\text{V}_{\text{CC}} = 380 \text{ V}$ $\text{I}_D = 27 \text{ A}$ $\text{V}_{\text{GS}} = 10 \text{ V}$ $\text{R}_G = 10 \Omega$ Inductive Load $T_C = 125^\circ\text{C}$	-	53	-	ns
$t_r$	Rise Time		-	16	-	ns
$t_{\text{d(off)}}$	Turn-Off Delay Time		-	257	-	ns
$t_f$	Fall Time		-	20	-	ns
$E_{\text{ON}}$	Turn-On Switching Loss per Pulse		-	719	-	$\mu\text{J}$
$E_{\text{OFF}}$	Turn-Off Switching Loss per Pulse		-	124	-	$\mu\text{J}$
$Q_g$	Total Gate Charge	$\text{V}_{\text{DS}} = 380 \text{ V}$ , $\text{V}_{\text{GS}} = 0 \text{ V} \dots +10 \text{ V}$ , $\text{I}_D = 27 \text{ A}$	-	155	-	nC
$R_{\theta\text{JC}}$	Thermal Resistance of Junction to Case	per Chip	-	-	0.5	$^\circ\text{C/W}$

## Typical Performance Characteristic

Fig 1. Typical Output Characteristics - IGBT

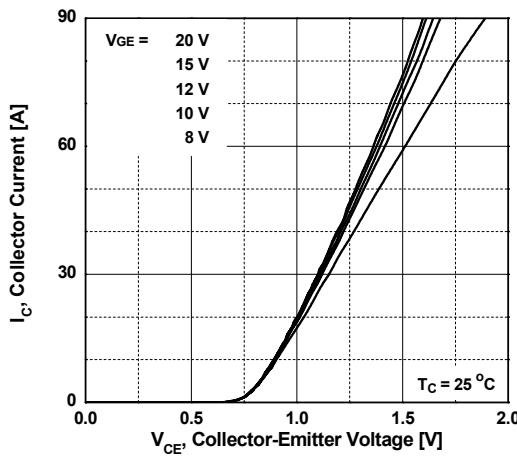


Fig 3. Typical Saturation Voltage Characteristics - IGBT

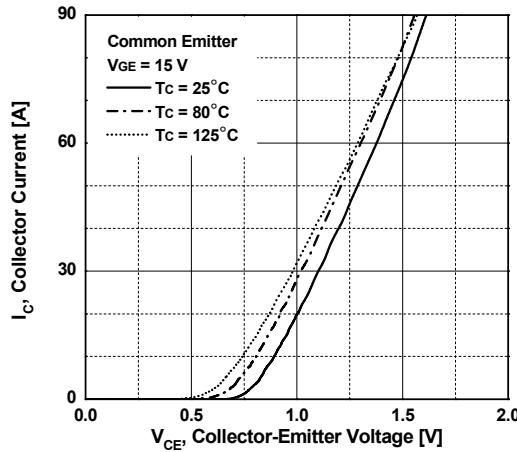


Fig 5. Typical Forward Voltage Drop vs. Forward Current - High-Side FWD

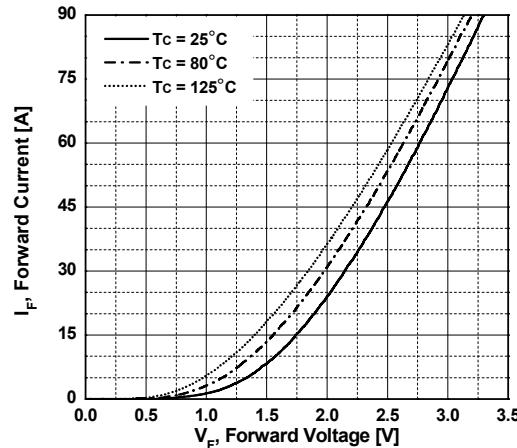


Fig 2. Typical Output Characteristics - IGBT

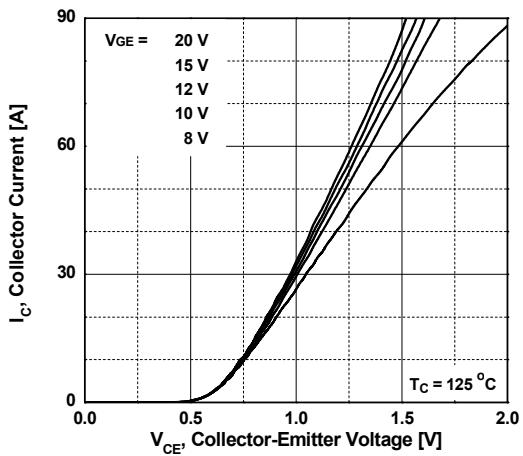


Fig 4. Transient Thermal Response Curve - IGBT

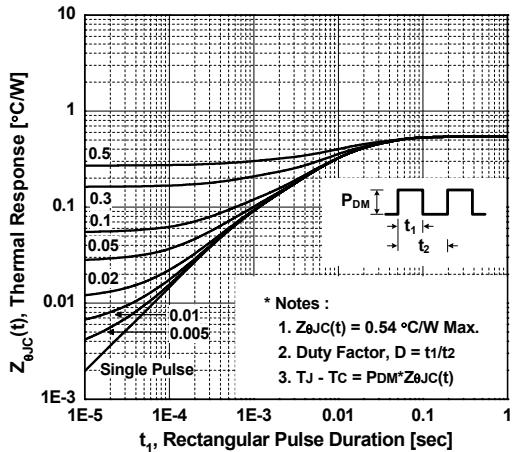
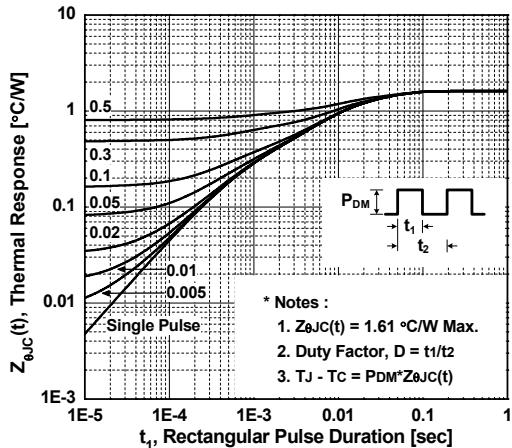


Fig 6. Transient Thermal Response Curve - High-Side FWD



## Typical Performance Characteristic (Continued)

Fig 7. On-Region Characteristics - MOSFET

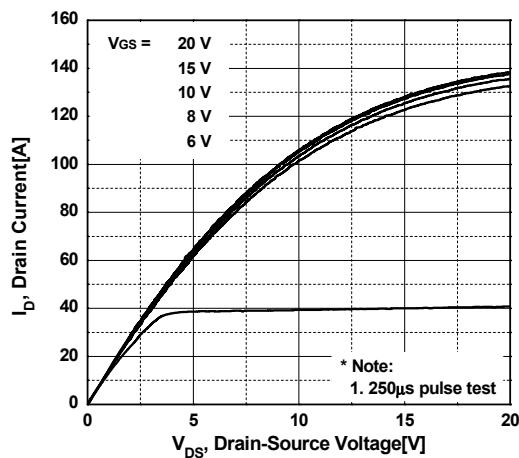


Fig 9. On-Resistance Variation vs. Temperature - MOSFET

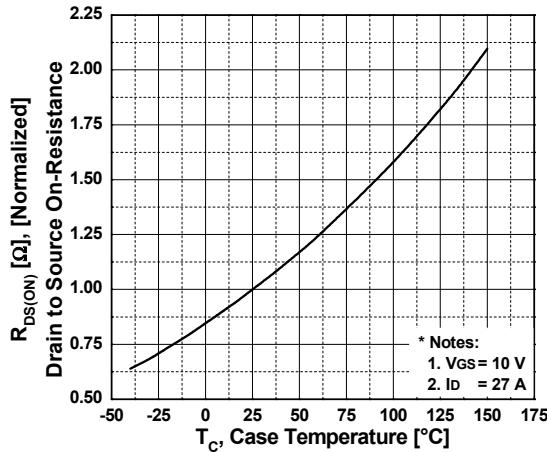


Fig 11. Turn-Off Loss vs. Gate Resistor Values - MOSFET

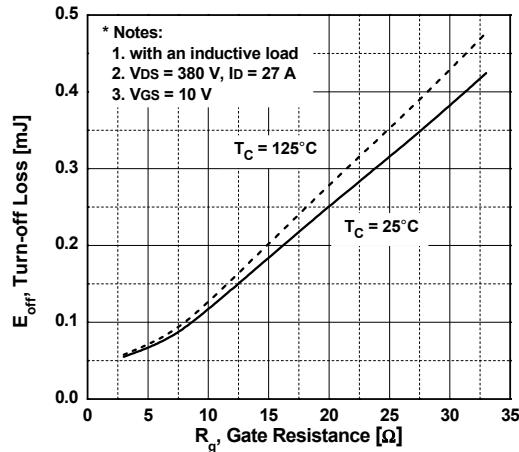


Fig 8. On-Resistance Variation vs. Drain Current and Gate Voltage - MOSFET

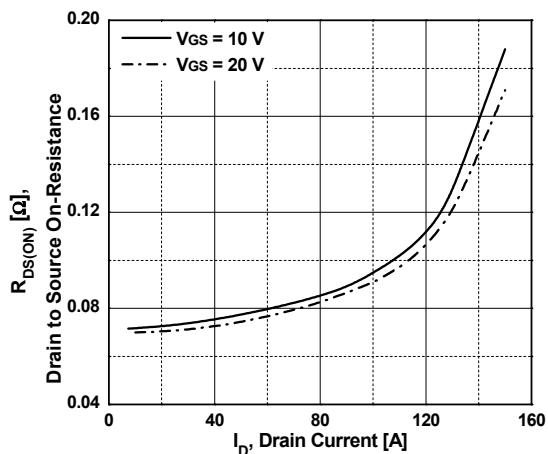


Fig 10. Body Diode Forward Voltage Variation vs. Source Current and Temperature - MOSFET

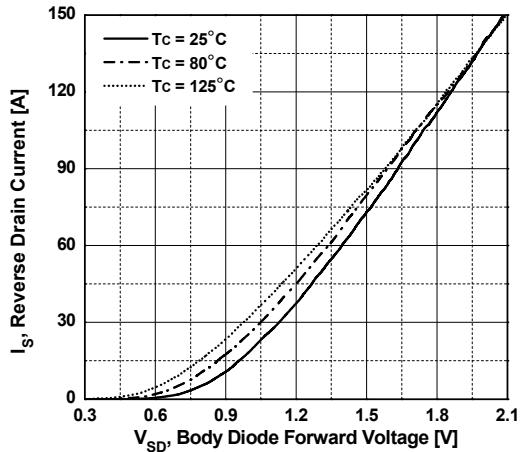
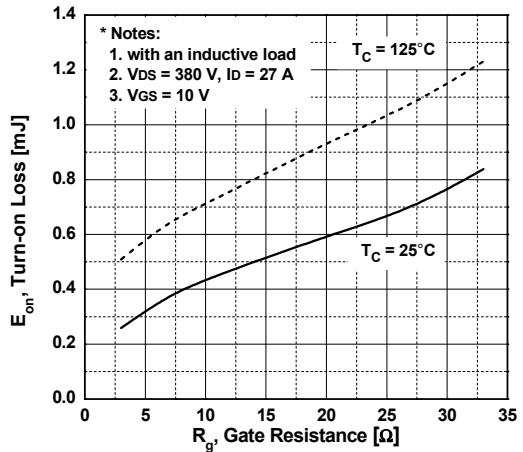


Fig 12. Turn-On Loss vs. Gate Resistor Values - MOSFET



## Typical Performance Characteristic (Continued)

Fig 13. Turn-Off Loss vs. Drain Current - MOSFET

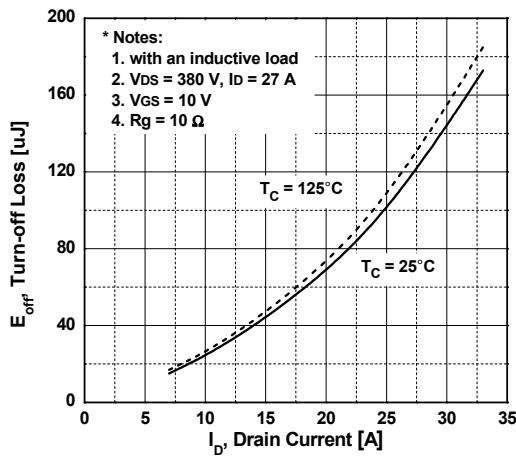


Fig 15. Transient Thermal Response Curve - MOSFET

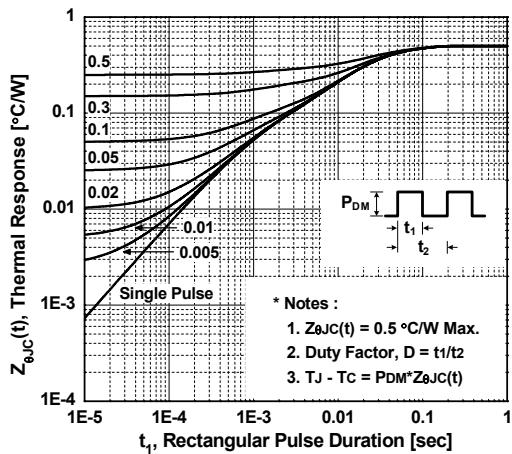


Fig 17. Transient Thermal Response Curve - Rectifier Diode

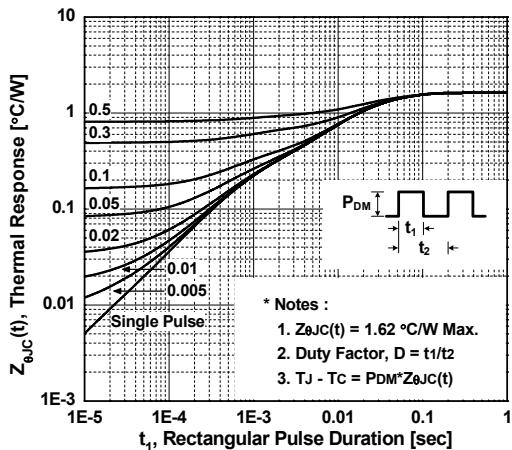


Fig 14. Turn-On Loss vs. Drain Current - MOSFET

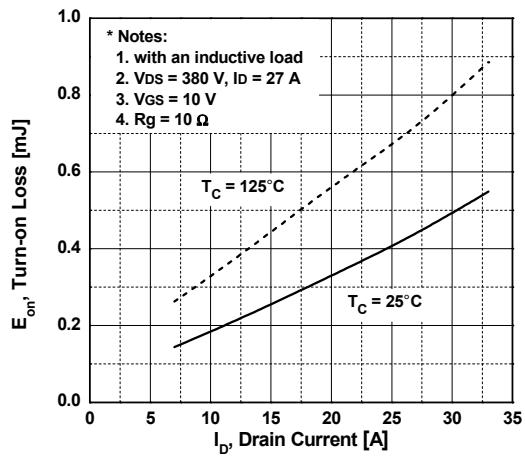
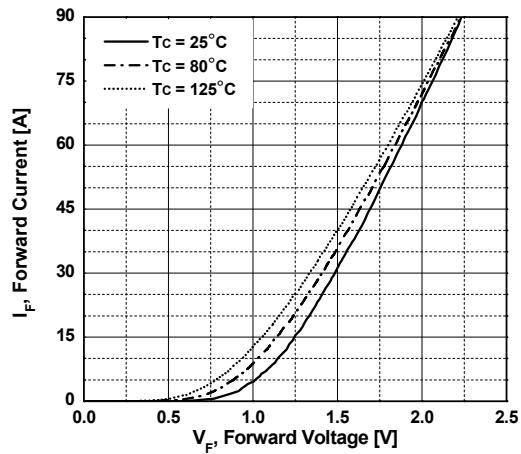
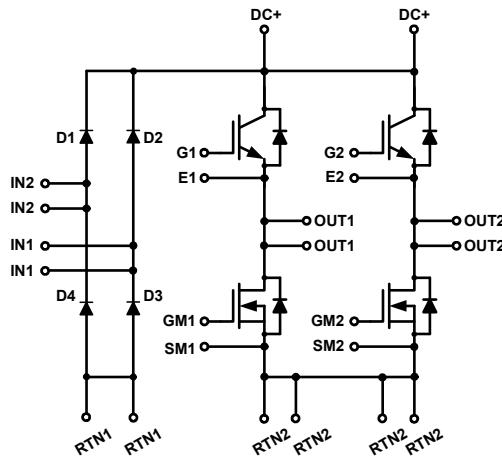


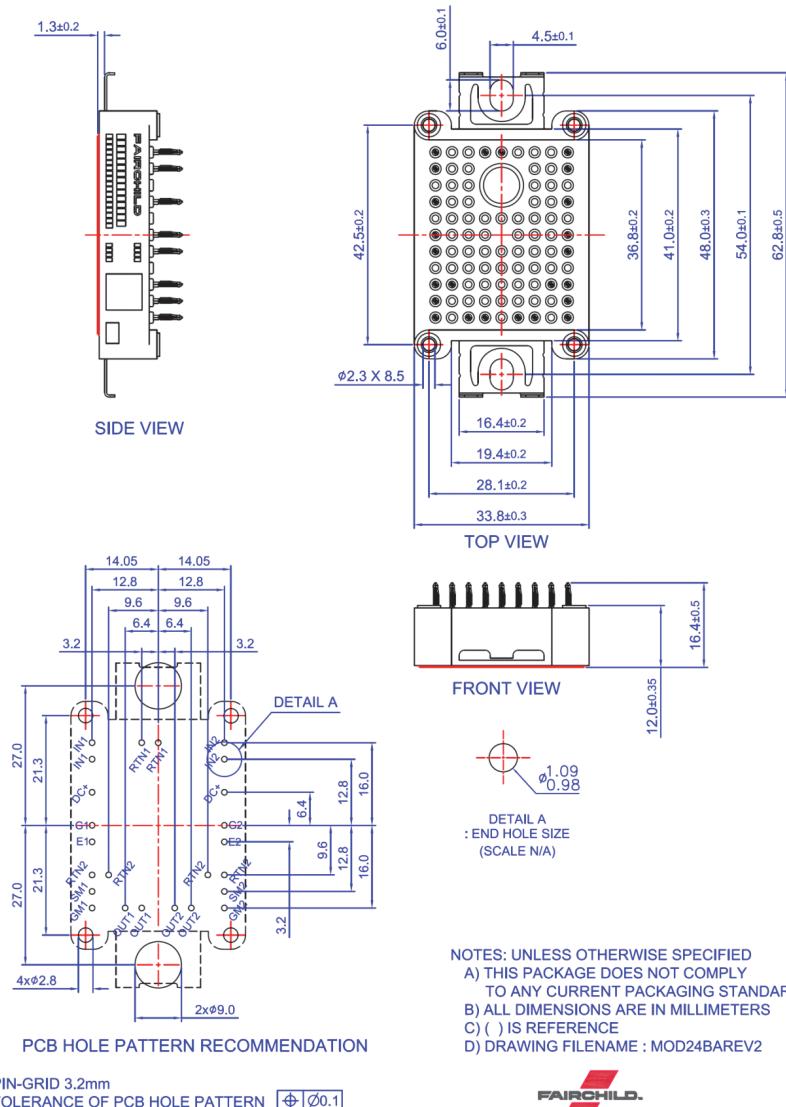
Fig 16. Typical Forward Voltage Drop vs. Forward Current - Rectifier Diode



## Internal Circuit Diagram



## Package Outlines [mm]



NOTES: UNLESS OTHERWISE SPECIFIED  
A) THIS PACKAGE DOES NOT COMPLY  
TO ANY CURRENT PACKAGING STANDARD  
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## PRODUCT STATUS DEFINITIONS

### Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
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Rev. I66

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